



VN750 / VN750S VN750PT / VN750-B5

HIGH SIDE DRIVER

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VN750 VN750S VN750PT VN750-B5	60 m Ω	6 A	36 V

- CMOS COMPATIBLE INPUT
- ON STATE OPEN LOAD DETECTION
- OFF STATE OPEN LOAD DETECTION
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- PROTECTION AGAINST LOSS OF GROUND
- VERY LOW STAND-BY CURRENT
- REVERSE BATTERY PROTECTION (*)

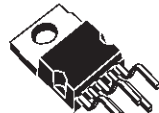
DESCRIPTION

The VN750, VN750S, VN750PT, VN750-B5 are a monolithic device designed in STMicroelectronics VIPower M0-3 Technology, intended for driving any kind of load with one side connected to ground.

Active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transient



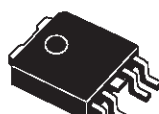
SO-8



PENTAWATT



P²PAK



PPAK

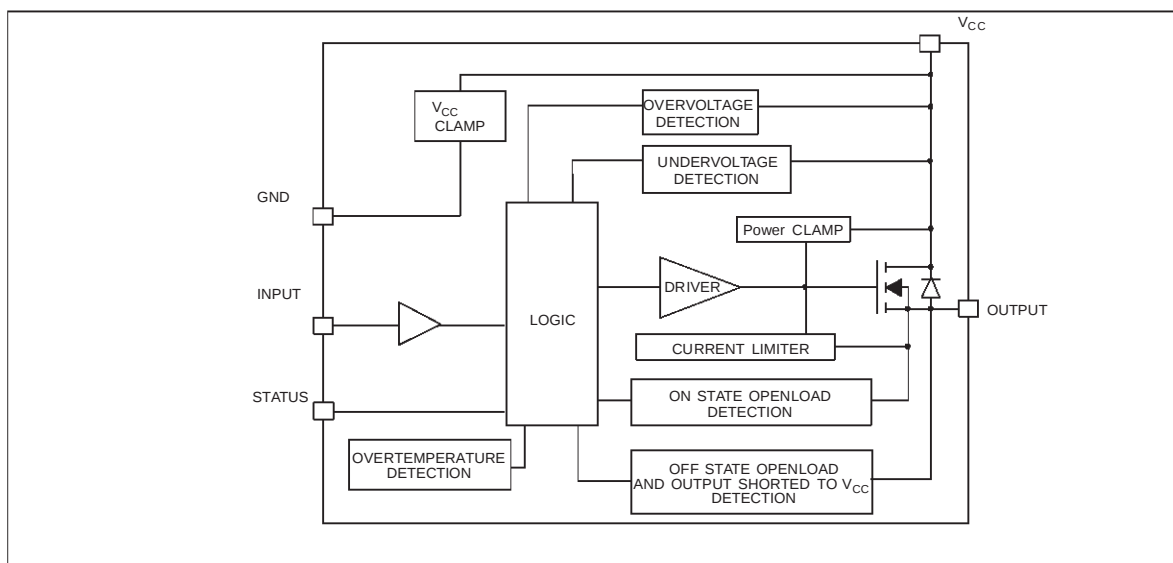
ORDER CODES :

PENTAWATT	VN750
SO-8	VN750S
P ² PAK	VN750-B5
PPAK	VN750PT

compatibility table). Active current limitation combined with thermal shutdown and automatic restart protect the device against overload.

The device detects open load condition both is on and off state. Output shorted to V_{CC} is detected in the off state. Device automatically turns off in case of ground pin disconnection.

BLOCK DIAGRAM

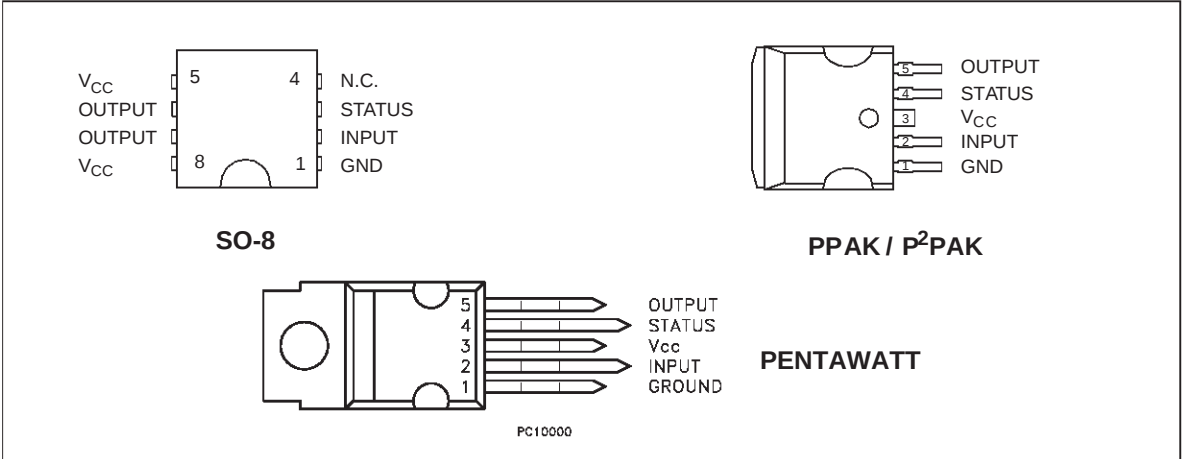


(*) See application schematic at page 8

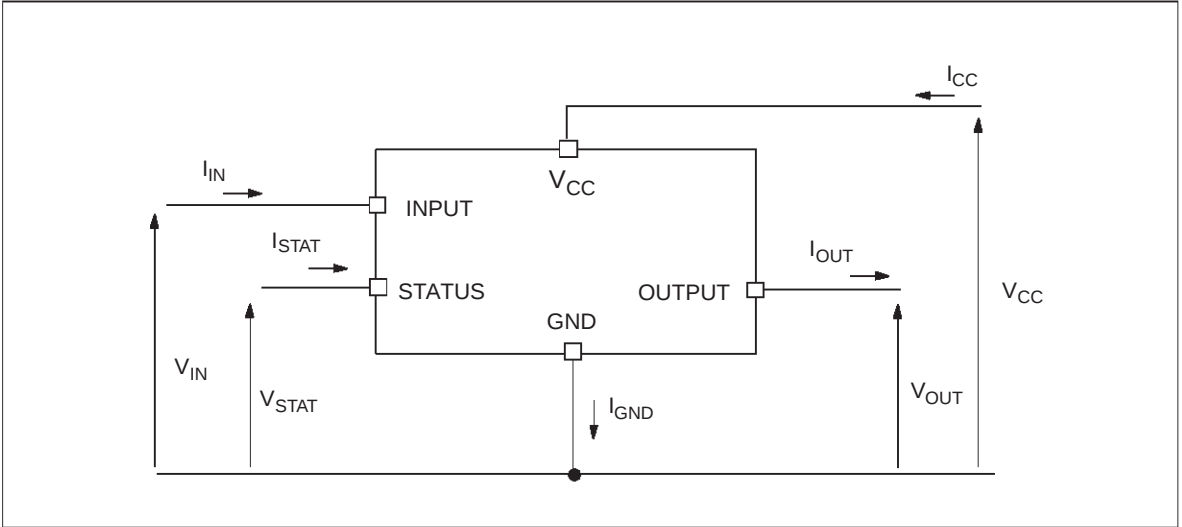
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value				Unit
		SO-8	PENTAWATT	P ² PAK	PPAK	
V_{CC}	DC Supply Voltage		41			V
$-V_{CC}$	Reverse DC Supply Voltage		- 0.3			V
$-I_{gnd}$	DC Reverse Ground Pin Current		- 200			mA
I_{OUT}	DC Output Current		Internally Limited			A
$-I_{OUT}$	Reverse DC Output Current		- 6			A
I_{IN}	DC Input Current		+/- 10			mA
I_{STAT}	DC Status Current		+/- 10			mA
V_{ESD}	Electrostatic Discharge (R=1.5K Ω ; C=100pF)		2000			V
P_{tot}	Power Dissipation $T_C=25^{\circ}C$	4.2	42	42	42	W
T_j	Junction Operating Temperature		Internally Limited			$^{\circ}C$
T_c	Case Operating Temperature		- 40 to 150			$^{\circ}C$
T_{stg}	Storage Temperature		- 55 to 150			$^{\circ}C$

CONNECTION DIAGRAM (TOP VIEW)



CURRENT AND VOLTAGE CONVENTIONS



THERMAL DATA

Symbol	Parameter		Value				Unit
			S0-8	PENTAWATT	P ² PAK	PPAK	
R _{thj-case}	Thermal Resistance Junction-case	Max	-	3	3	3	°C/W
R _{thj-lead}	Thermal Resistance Junction-lead	Max	30	-	-	-	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	80 (*)	60 (**)	53 (**)	53 (**)	°C/W

(*) When mounted on a standard single-sided FR-4 board with 50mm² of Cu (at least 35μm thick) connected to all V_{CC} pins.

(**) When mounted on a standard single-sided FR-4 board with 50mm² of Cu (at least 35μm thick).

ELECTRICAL CHARACTERISTICS (8V < V_{CC} < 36V; -40°C < T_j < 150°C unless otherwise specified)

POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{CC}	Operating Supply Voltage		5.5	13	36	V
V _{USD}	Undervoltage Shut-down		3	4	5.5	V
V _{USDhyst}	Undervoltage Shut-down Hysteresis			0.5		V
V _{OV}	Overvoltage Shut-down		36	42	48	V
R _{ON}	On State Resistance	I _{OUT} =2A; T _j =25°C; V _{CC} >8V I _{OUT} =2A; V _{CC} >8V		(*)	60 120	mΩ mΩ
I _S	Supply Current	Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V; T _j =25°C On State; V _{CC} =13V; V _{IN} =5V; I _{OUT} =0A		10 10 2	25 20 3.5	μA μA mA
I _{L(off1)}	Off State Output Current	V _{IN} =V _{OUT} =0V	0	(*)	50	μA
I _{L(off2)}	Off State Output Current	V _{IN} =0V; V _{OUT} =3.5V	-75		0	μA

SWITCHING (V_{CC}=13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)}	Turn-on Delay Time	R _L =6.5Ω from V _{IN} rising edge to V _{OUT} =1.3V		40		μs
t _{d(off)}	Turn-off Delay Time	R _L =6.5Ω from V _{IN} falling edge to V _{OUT} =11.7V		30		μs
dV _{OUT} /dt _(on)	Turn-on Voltage Slope	R _L =6.5Ω from V _{OUT} =1.3V to V _{OUT} =10.4V		(*)		V/μs
dV _{OUT} /dt _(off)	Turn-off Voltage Slope	R _L =6.5Ω from V _{OUT} =11.7V to V _{OUT} =1.3V		(*)		V/μs

INPUT PIN

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{IL}	Input Low Level			(*)	1.25	V
I _{IL}	Low Level Input Current	V _{IN} =1.25V	1	(*)		μA
V _{IH}	Input High Level		3.25	(*)		V
I _{IH}	High Level Input Current	V _{IN} =3.25V		(*)	10	μA
V _{hyst}	Input Hysteresis Voltage		0.5	(*)		V
V _{ICL}	Input Clamp Voltage	I _{IN} =1mA I _{IN} =-1mA	6	6.8 -0.7	8	V V

(*) See curves at pages 9, 10, 11

ELECTRICAL CHARACTERISTICS (continued)

STATUS PIN

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{STAT}	Status Low Output Voltage	$I_{STAT}=1.6\text{mA}$		(*)	0.5	V
I_{LSTAT}	Status Leakage Current	Normal Operation; $V_{STAT}=5\text{V}$		(*)	10	μA
C_{STAT}	Status Pin Input Capacitance	Normal Operation; $V_{STAT}=5\text{V}$			100	pF
V_{SCL}	Status Clamp Voltage	$I_{STAT}=1\text{mA}$	6	6.8	8	V
		$I_{STAT}=-1\text{mA}$		-0.7		V

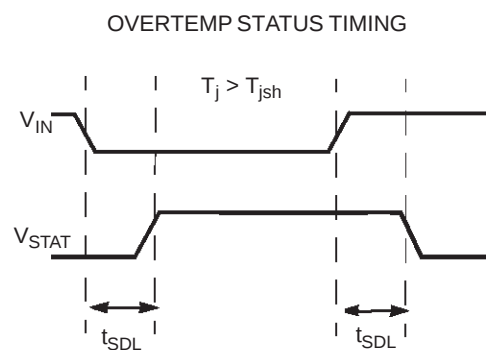
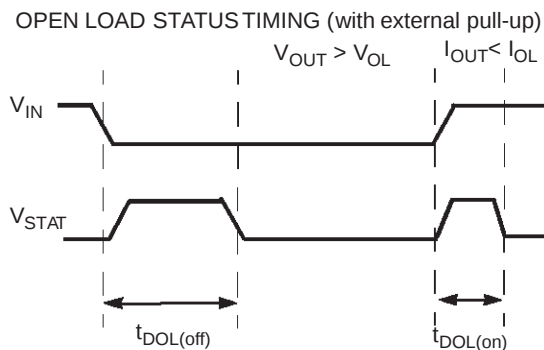
PROTECTIONS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T_{TSD}	Shut-down Temperature		150	175	200	$^{\circ}\text{C}$
T_R	Reset Temperature		135			$^{\circ}\text{C}$
T_{hyst}	Thermal Hysteresis		7	15		$^{\circ}\text{C}$
t_{SDL}	Status delay in overload condition	$T_j > T_{jsh}$			20	μs
I_{lim}	Current limitation	$9\text{V} < V_{CC} < 36\text{V}$	6	9	15	A
		$5\text{V} < V_{CC} < 36\text{V}$			15	A
V_{demag}	Turn-off Output Clamp Voltage	$I_{OUT}=2\text{A}$; $V_{IN}=0\text{V}$; $L=6\text{mH}$	$V_{CC}-41$	$V_{CC}-48$	$V_{CC}-55$	V

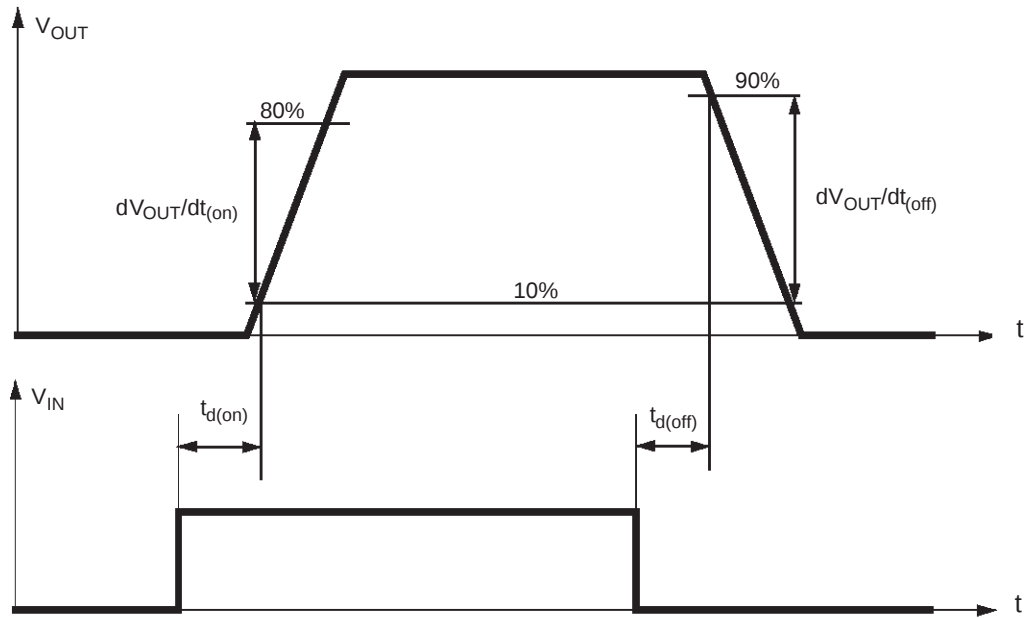
OPENLOAD DETECTION

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_{OL}	Openload ON State Detection Threshold	$V_{IN}=5\text{V}$	50	(*)	200	mA
$t_{DOL(on)}$	Openload ON State Detection Delay	$I_{OUT}=0\text{A}$			200	μs
V_{OL}	Openload OFF State Voltage Detection Threshold	$V_{IN}=0\text{V}$	1.5	(*)	3.5	V
$t_{DOL(off)}$	Openload Detection Delay at Turn Off				1000	μs

(*) See curves at pages 9, 10, 11



Switching time Waveforms



TRUTH TABLE

CONDITIONS	INPUT	OUTPUT	STATUS
Normal Operation	L	L	H
	H	H	H
Current Limitation	L	L	H
	H	X	H
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output Voltage > V_{OL}	L	H	L
	H	H	H
Output Current < I_{OL}	L	L	H
	H	H	L

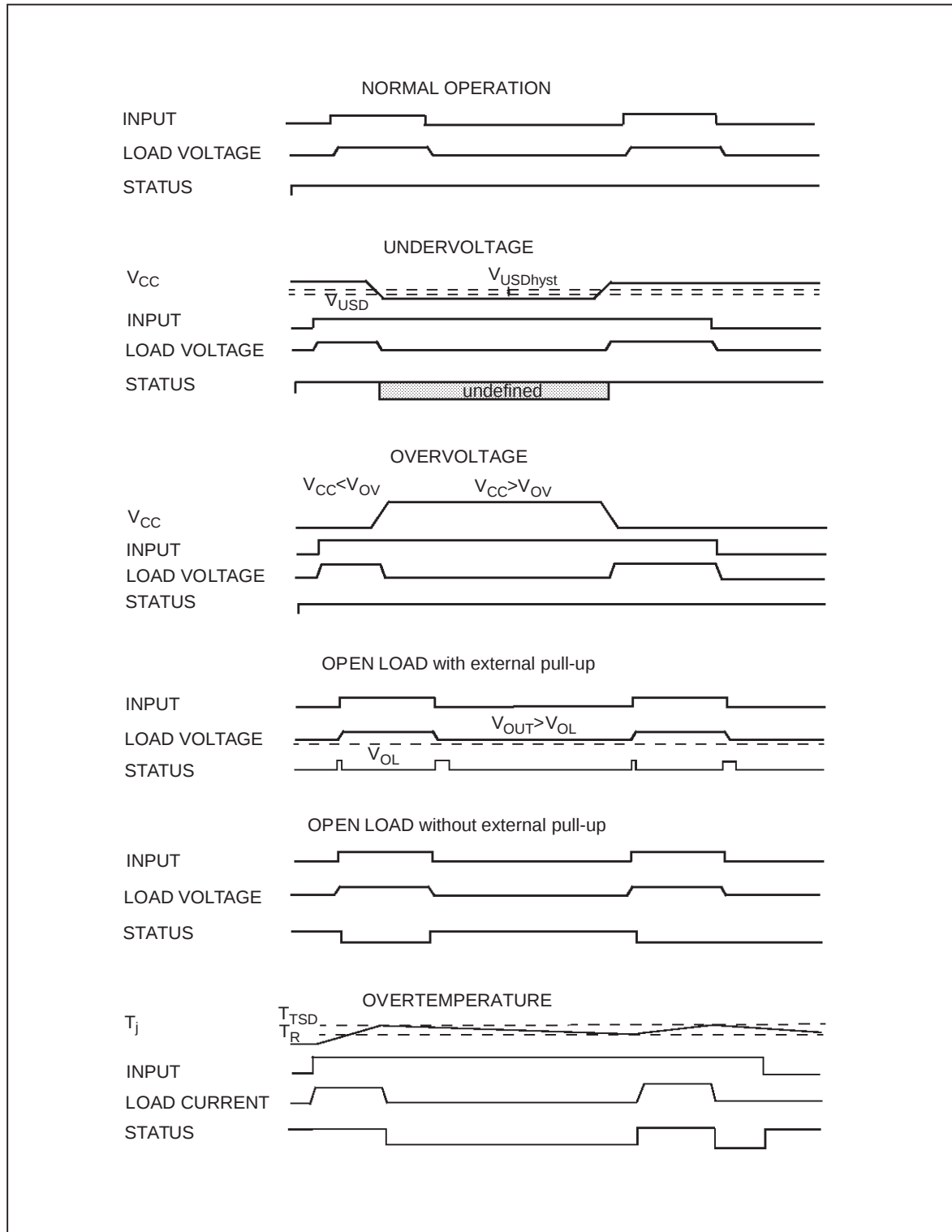
ELECTRICAL TRANSIENT REQUIREMENTS ON V_{CC} PIN

ISO T/R 7637/1 Test Pulse	TEST LEVELS				
	I	II	III	IV	Delays and Impedance
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 μs 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 μs 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

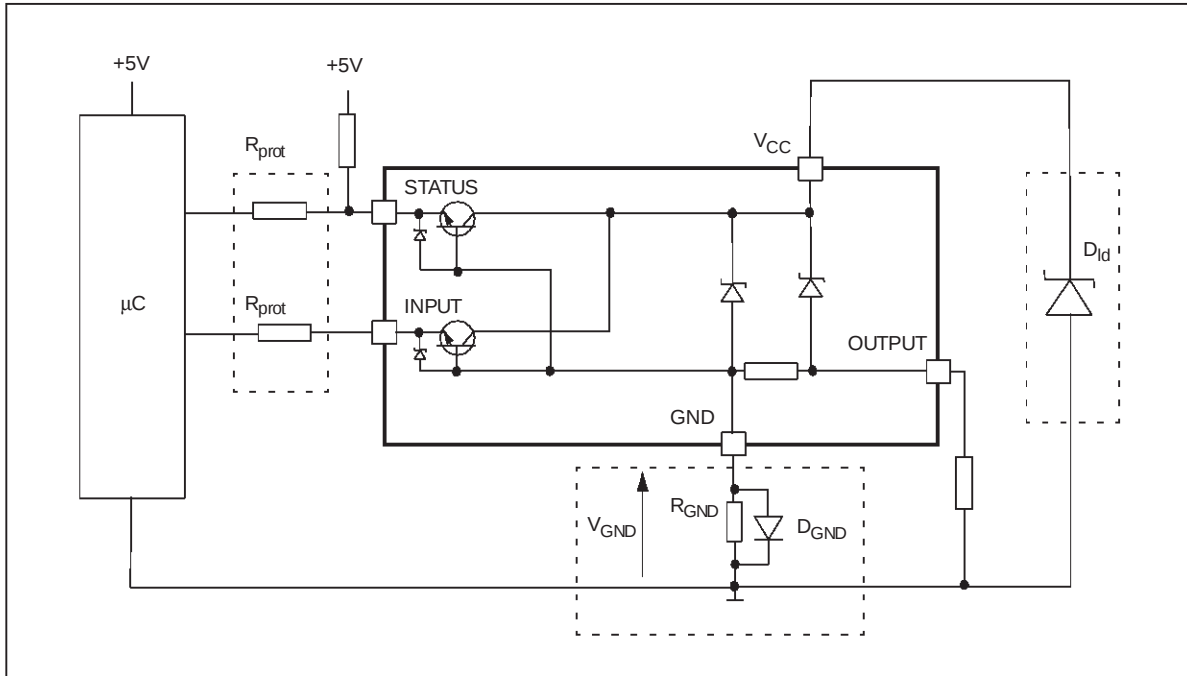
ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

Figure1: Waveforms



APPLICATION SCHEMATIC

**GND PROTECTION NETWORK AGAINST REVERSE BATTERY**

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

- 1) $R_{GND} \leq 600\text{mV} / (I_{S(on)max})$.
- 2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2 (see below).

Solution 2: A diode (D_{GND}) in the ground line.

A resistor ($R_{GND} = 1\text{k}\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift (j 600mV) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

LOAD DUMP PROTECTION

D_{ld} is necessary (Transil or MOV) if the load dump peak voltage exceeds V_{CC} max DC rating. The same applies if the device will be subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

μC I/Os PROTECTION:

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the μC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of μC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of μC I/Os.

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

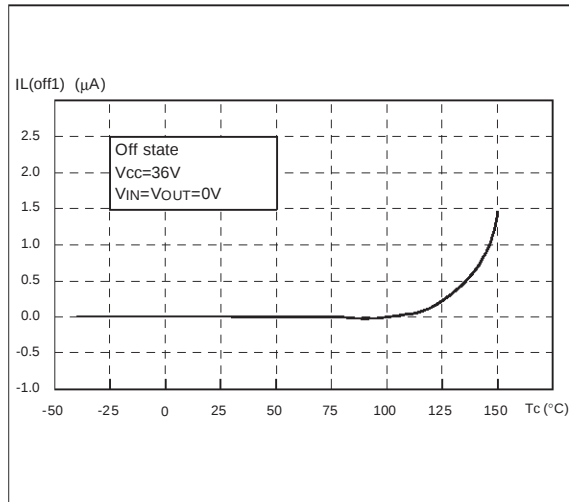
Calculation example:

For $V_{CCpeak} = -100\text{V}$ and $I_{latchup} \geq 20\text{mA}$; $V_{OH\mu C} \geq 4.5\text{V}$

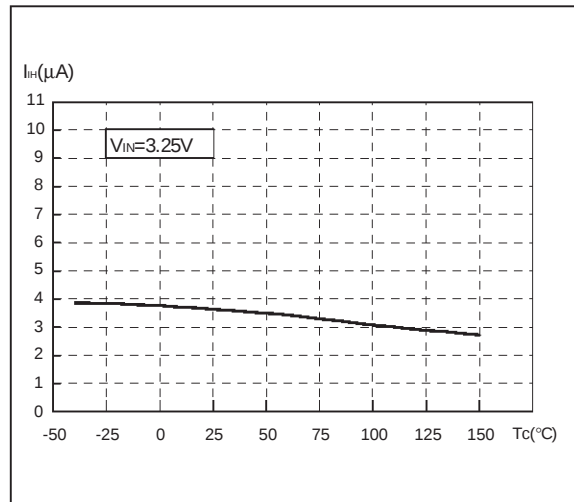
$$5\text{k}\Omega \leq R_{prot} \leq 65\text{k}\Omega$$

Recommended R_{prot} value is $10\text{k}\Omega$.

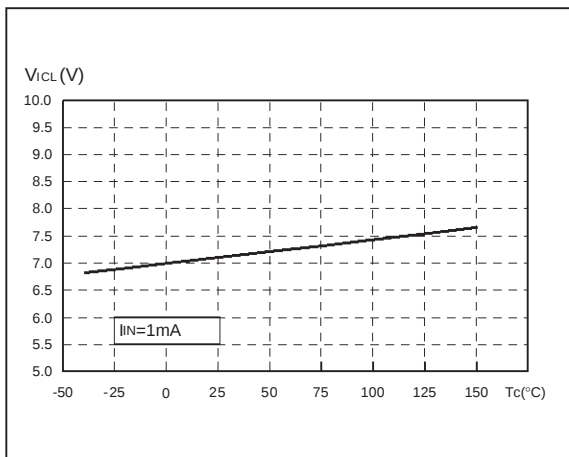
Off State Output Current



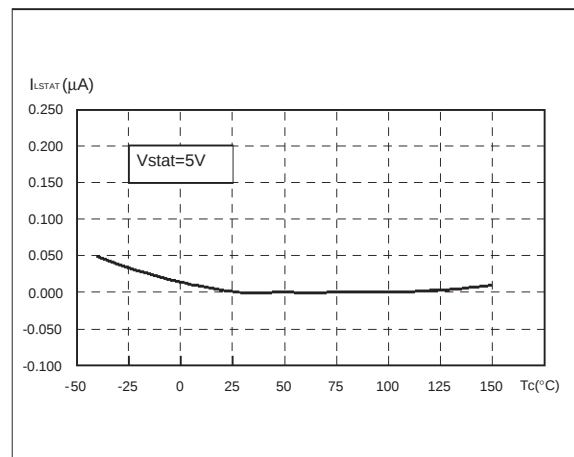
High Level Input Current



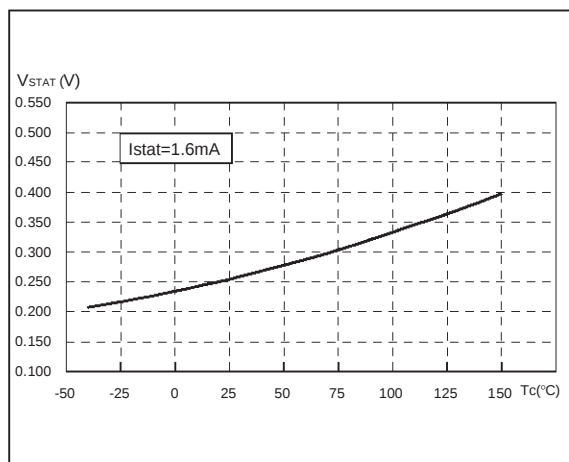
Input Clamp Voltage



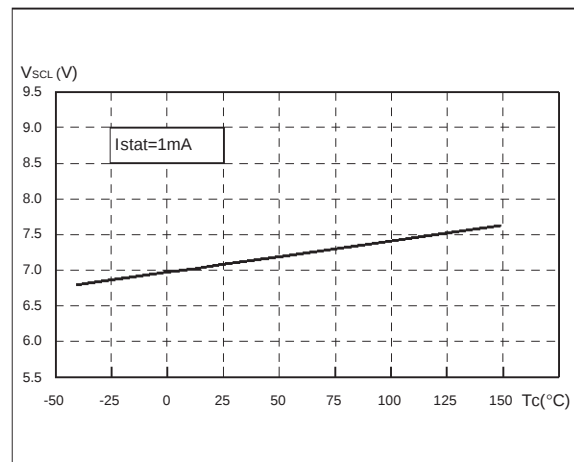
Status Leakage Current



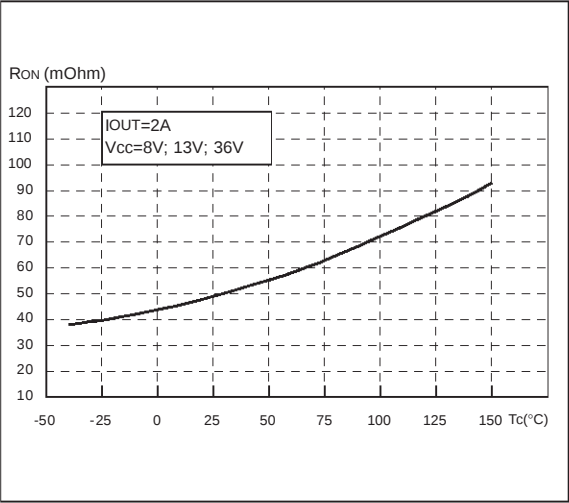
Status Low Output Voltage



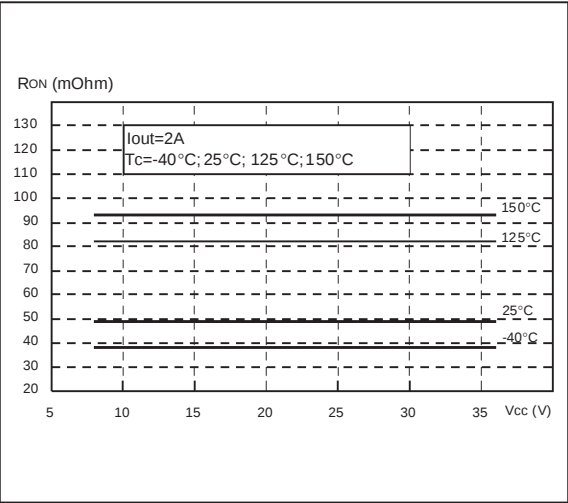
Status Clamp Voltage



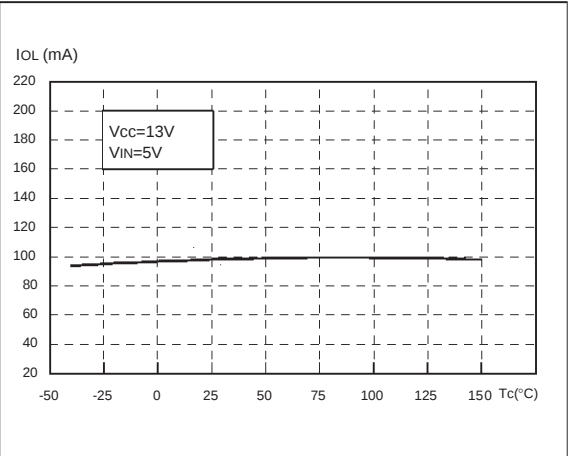
On State Resistance Vs T_{case}



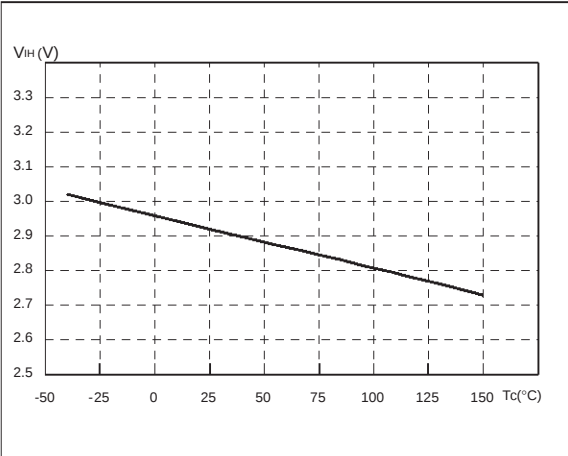
On State Resistance Vs V_{CC}



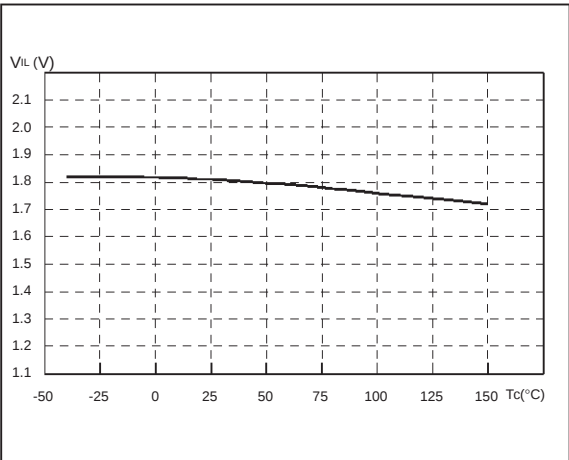
Openload On State Detection Threshold



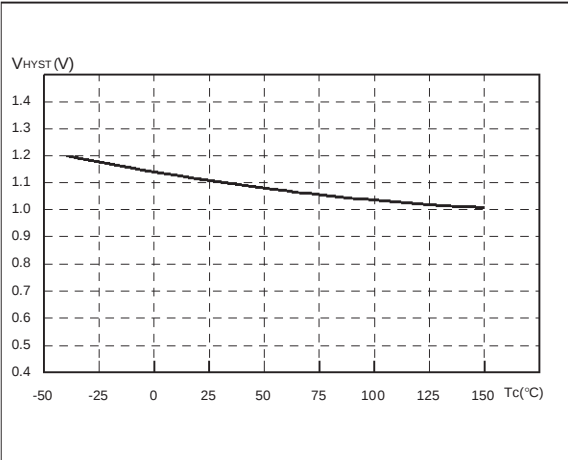
Input High Level



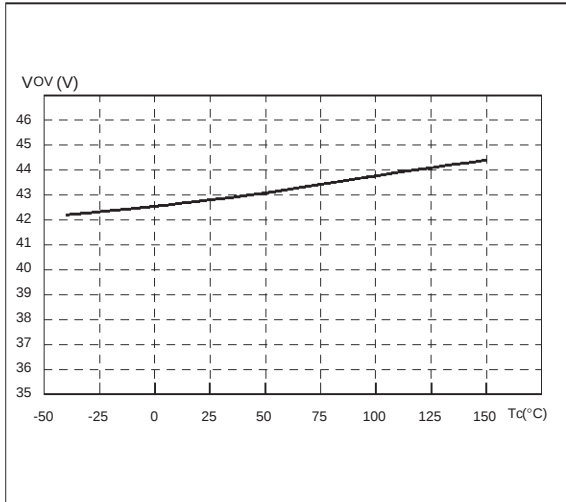
Input Low Level



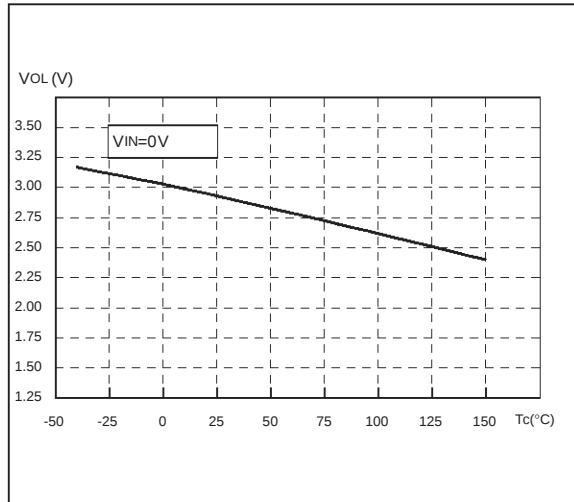
Input Hysteresis Voltage



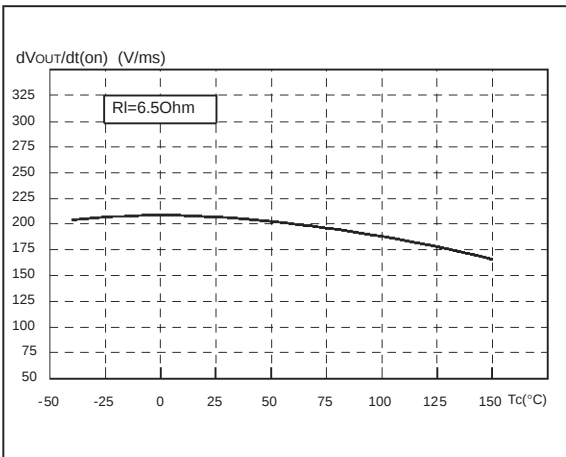
Overvoltage Shutdown



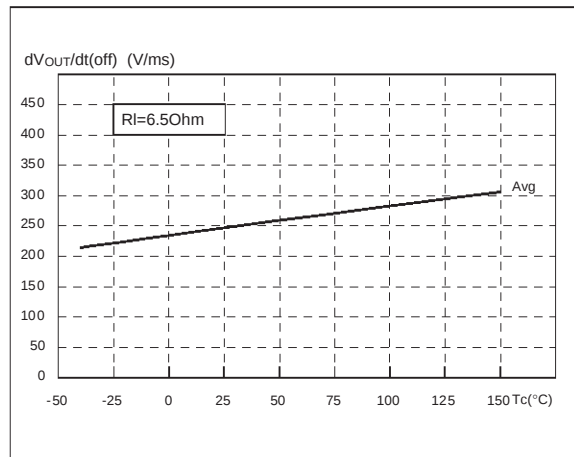
Openload Off State Voltage Detection Threshold



Turn-on Voltage Slope

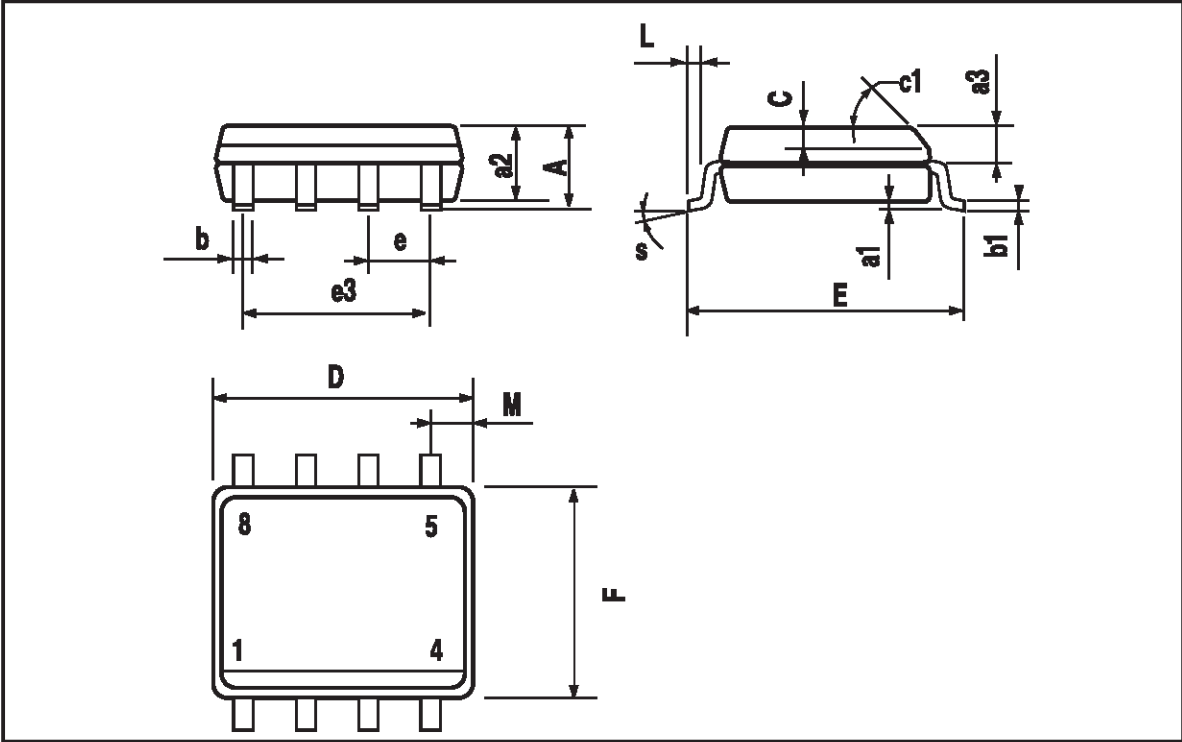


Turn-off Voltage Slope



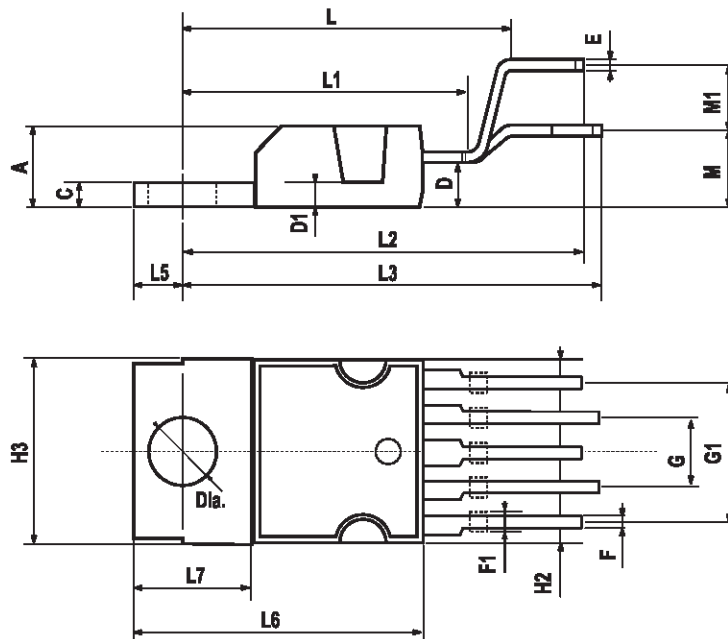
SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					
L1	0.8		1.2	0.031		0.047



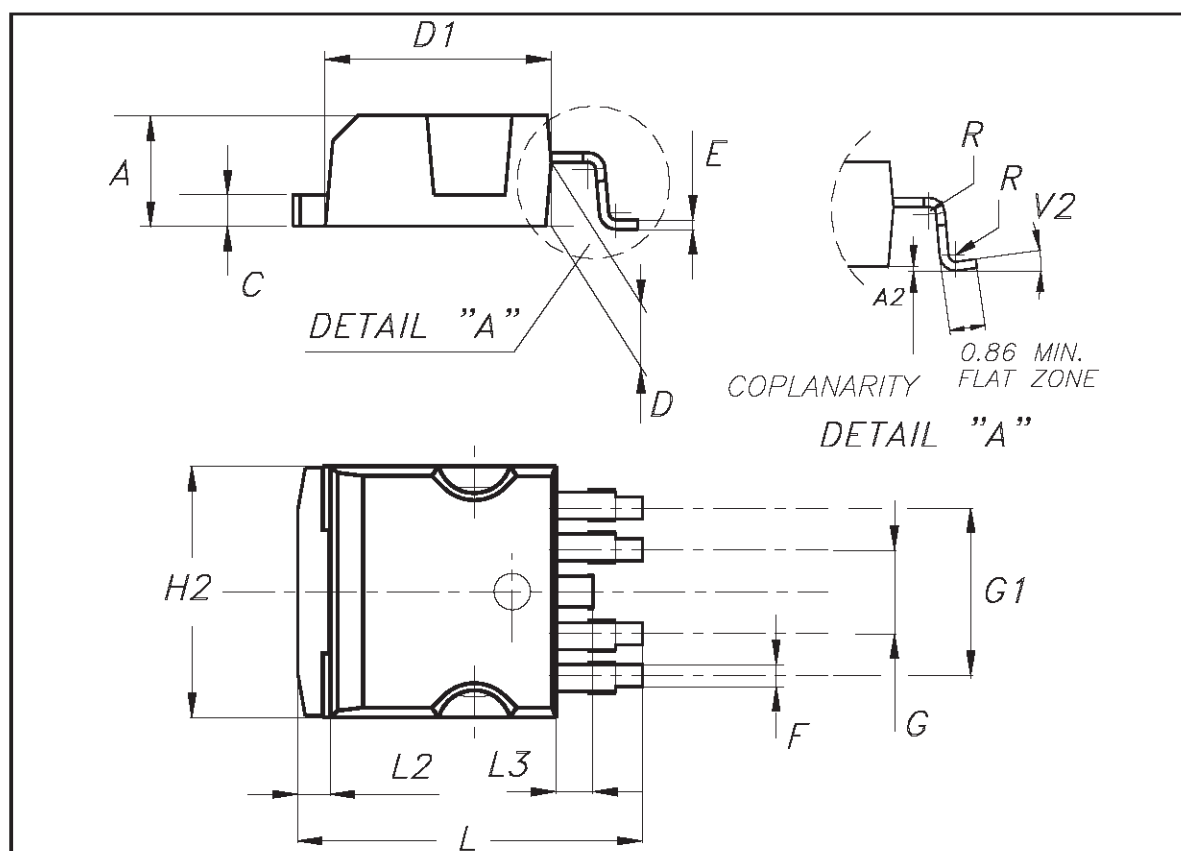
PENTAWATT (VERTICAL) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.8		1.05	0.031		0.041
F1	1		1.4	0.039		0.055
G	3.2	3.4	3.6	0.126	0.134	0.142
G1	6.6	6.8	7	0.260	0.268	0.276
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		17.85			0.703	
L1		15.75			0.620	
L2		21.4			0.843	
L3		22.5			0.886	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		4.5			0.177	
M1		4			0.157	
Diam.	3.65		3.85	0.144		0.152



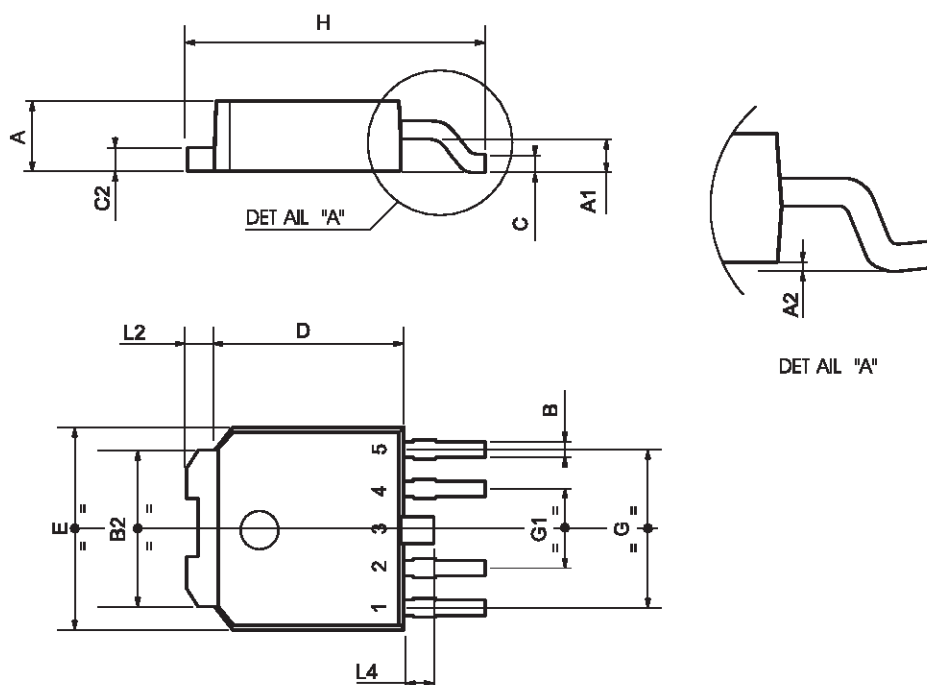
P²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.30		4.80	0.169		0.189
A2	0.03		0.23	0.001		0.009
C	1.17		1.37	0.046		0.054
D	2.40		2.80	0.094		0.110
D1	8.95		9.35	0.352		0.368
E	0.35		0.55	0.014		0.022
F	0.80		1.05	0.031		0.041
G	3.20		3.60	0.126		0.142
G1	6.60		7.00	0.260		0.276
H2			10.40			0.409
L	13.59		14.39	0.535		0.567
L2	1.27		1.40	0.050		0.055
L3	1.30		1.70	0.051		0.067
R		0.30			0.012	
V2	0 d		8 d			

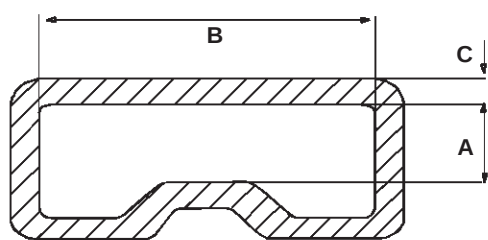


PPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.4		0.6	0.015		0.023
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.9		5.25	0.193		0.206
G1	2.38		2.7	0.093		0.106
H	9.35		10.1	0.368		0.397
L2		0.8	1		0.031	0.039
L4	0.6		1	0.031		0.039



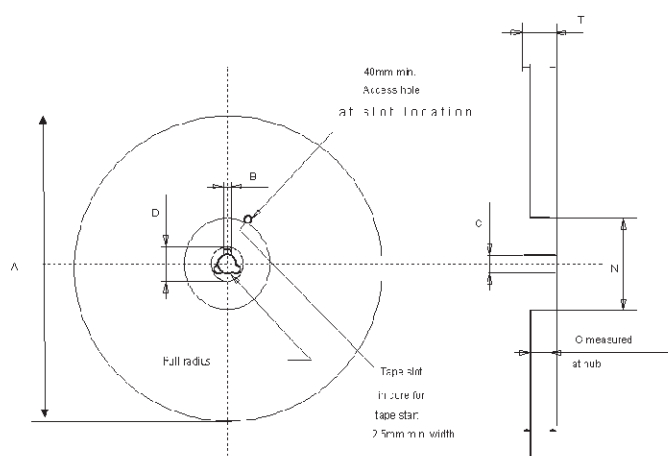
SO-8 TUBE SHIPMENT (no suffix)



Base Q.ty	100
Bulk Q.ty	2000
Tube length (± 0.5)	532
A	3.2
B	6
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

Base Q.ty	2500
Bulk Q.ty	2500
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+ 2 / - 0)	12.4
N (min)	60
T (max)	18.4

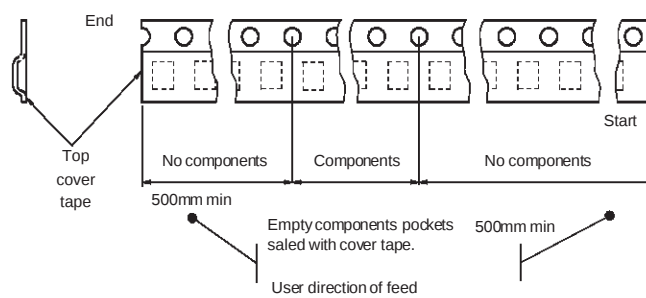
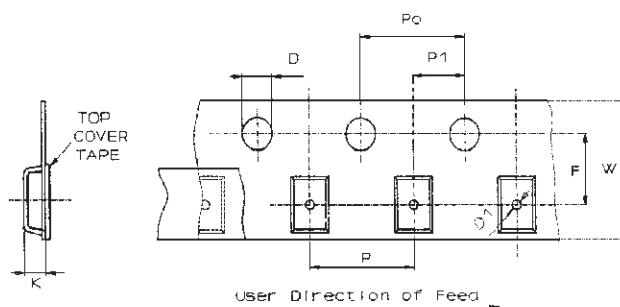
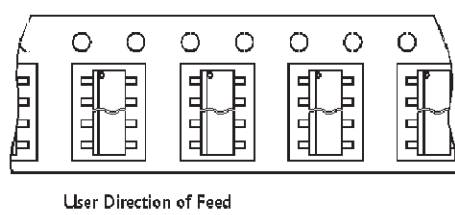
All dimensions are in mm.

TAPE DIMENSIONS

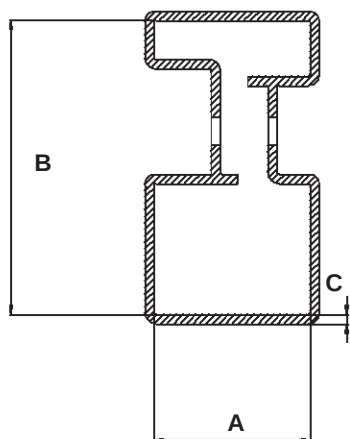
According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	12
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	8
Hole Diameter	D ($\pm 0.1/-0$)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	5.5
Compartment Depth	K (max)	4.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.



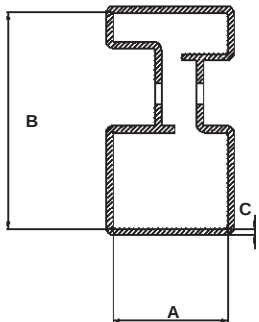
PENTAWATT TUBE SHIPMENT (no suffix)



Base Q.ty	50
Bulk Q.ty	1000
Tube length (± 0.5)	532
A	18
B	33.1
C (± 0.1)	1

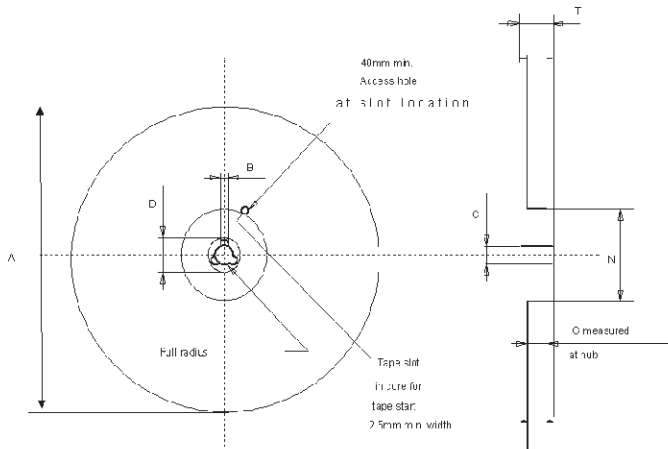
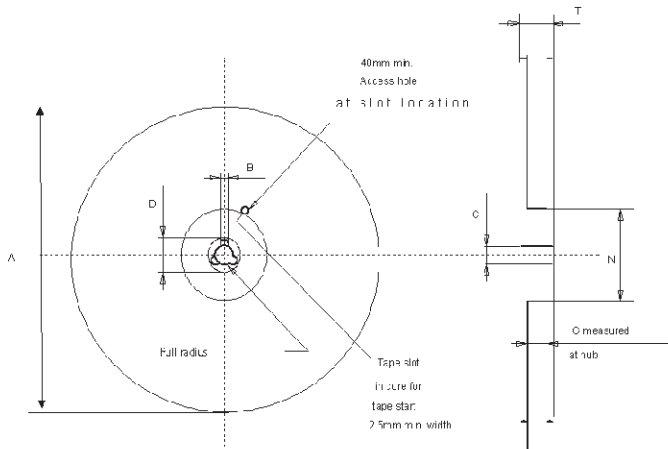
All dimensions are in mm.

P²PAK TUBE SHIPMENT (no suffix)

	Base Q.ty	50
	Bulk Q.ty	1000
	Tube length (± 0.5)	532
	A	18
	B	33.1
	C (± 0.1)	1

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")

	REEL DIMENSIONS	
	Base Q.ty	1000
	Bulk Q.ty	1000
	A (max)	330
	B (min)	1.5
	C (± 0.2)	13
	F	20.2
	G (+ 2 / - 0)	24.4
	N (min)	60
	T (max)	30.4

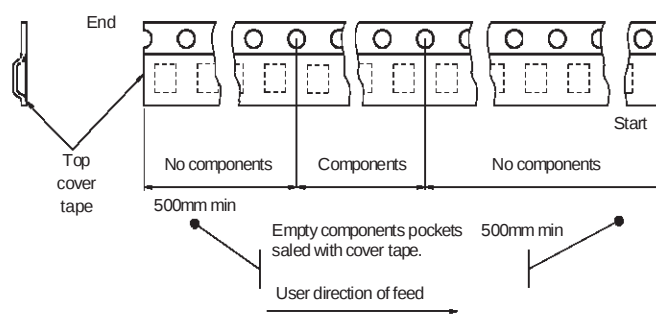
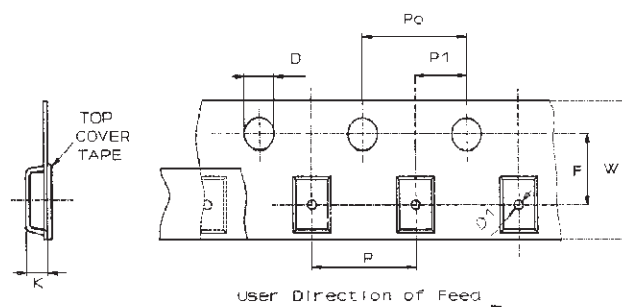
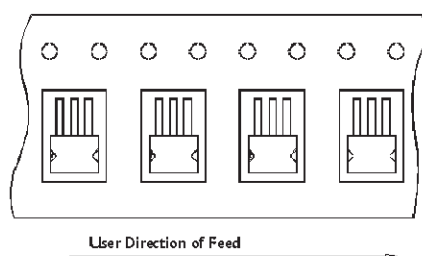
All dimensions are in mm.

TAPE DIMENSIONS

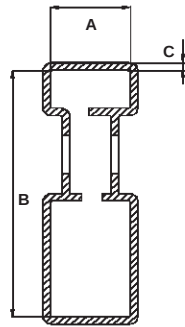
According to Electronic Industries Association
(EIA) Standard 481 rev. A, Feb 1986

Tape width	W	24
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	16
Hole Diameter	D ($\pm 0.1/-0$)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	11.5
Compartment Depth	K (max)	6.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.



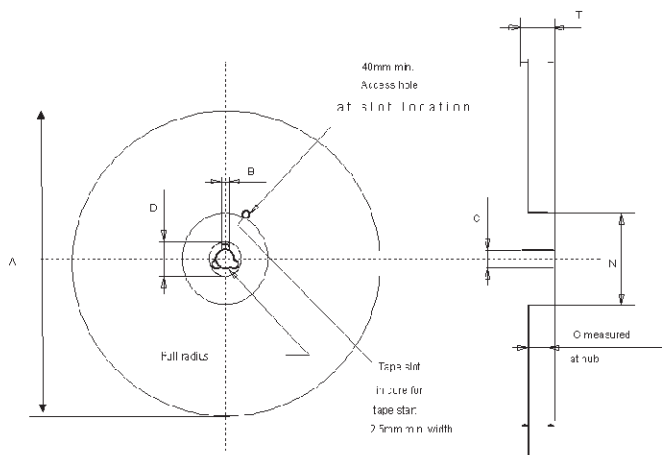
PPAK TUBE SHIPMENT (no suffix)



Base Q.ty	75
Bulk Q.ty	3000
Tube length (± 0.5)	532
A	6
B	21.3
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

Base Q.ty	2500
Bulk Q.ty	2500
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+2 / -0)	16.4
N (min)	60
T (max)	22.4

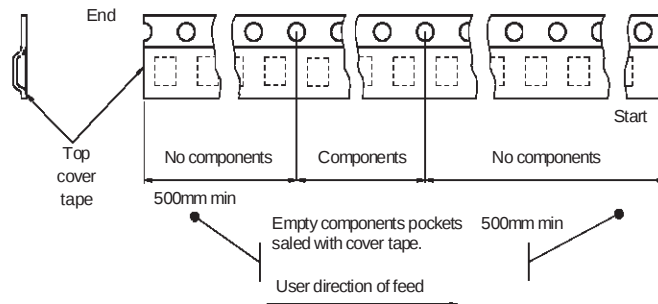
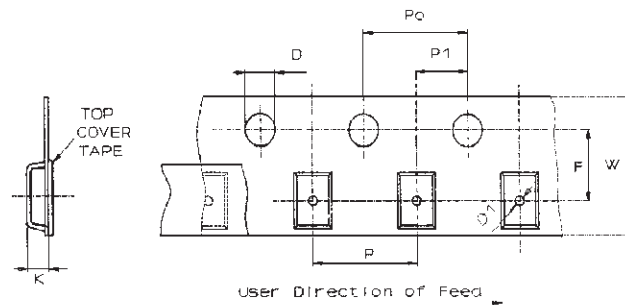
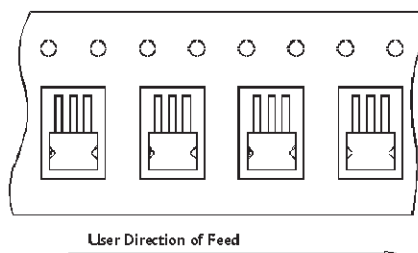
All dimensions are in mm.

TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	16
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	8
Hole Diameter	D ($\pm 0.1/-0$)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	7.5
Compartment Depth	K (max)	6.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.



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